

*trans*-Tetrabromobis(dimethylamine)tinCole Ritter III, Thomas L. Groy  
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## Key indicators

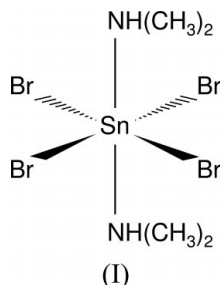
Single-crystal X-ray study  
 $T = 298$  K  
Mean  $\sigma(\text{N}-\text{C}) = 0.005$  Å  
 $R$  factor = 0.025  
 $wR$  factor = 0.065  
Data-to-parameter ratio = 21.9For details of how these key indicators were  
automatically derived from the article, see  
<http://journals.iucr.org/e>.

The title compound,  $[\text{SnBr}_4(\text{C}_2\text{H}_7\text{N})_2]$ , consists of separate centrosymmetric molecules with nearly octahedral geometry, in which the central Sn metal is surrounded by four Br atoms and two dimethylamine ligands. The unique Sn–N bond length is 2.244 (3) Å and the two Sn–Br lengths are 2.5867 (11) and 2.5707 (12) Å. The C–N bond lengths of the amine ligand are 1.482 (6) and 1.492 (6) Å. The unique angle in the  $\text{SnBr}_4$  plane is  $90.82(3)^\circ$ , and the axial to equatorial angles are  $86.18(10)$  and  $85.46(10)^\circ$ .

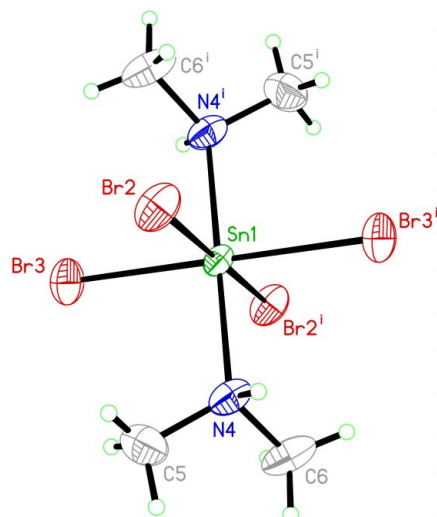
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## Comment

Recently, we have utilized reactions between common germanium hydrides and  $\text{SnD}_4$  to grow epitaxial layers of  $\text{Ge}_{1-x}\text{Sn}_x$  semiconductors on Si(100) substrates. The bandgaps of these materials are intermediate between those of Ge ( $E_g = 0.066$  eV) and Sn ( $E_g = 0.1$  eV), and decrease monotonically with increasing Sn concentration in the alloy, indicating that this material will have important application in Si-based devices, such as IR photodetectors. The application of pure  $\text{SnD}_4$  is the essential component in the preparation of these metastable and technologically important materials.  $\text{SnD}_4$  is synthesized by reduction of  $\text{SnBr}_4$  with  $\text{LiAlD}_4$  and it is typically isolated as a volatile liquid, which is unstable at room temperature with respect to Sn and  $\text{D}_2$ . Nevertheless, mixtures of the compound with high-purity  $\text{H}_2$  have the necessary stability at 295 K to be used as viable CVD sources in deposition of  $\text{Ge}_{1-x}\text{Sn}_x$  (Bauer, Taraci *et al.*, 2002). Ongoing efforts to further stabilize  $\text{SnD}_4$  by adduct formation with simple Lewis bases, such as dimethylamine, have led to the synthesis of the previously unknown complex  $\text{SnBr}_4[\text{HN}(\text{CH}_3)_2]_2$ . This compound is currently utilized to prepare the corresponding  $\text{SnH}_4$  and  $\text{SnD}_4$  derivatives as viable low-temperature CVD precursors of Sn.



The central Sn metal of the title compound is sixfold coordinated, with four Br atoms arranged in square-planar fashion and the two amine ligands nearly perpendicular to the  $\text{SnBr}_4$  plane (Fig. 1). The Sn–Br bond distances are



**Figure 1**  
Displacement ellipsoid plot shown at the 50% probability level [symmetry code: (i)  $-x, -y, -z$ ].

2.5867 (11) (Sn1—Br2) and 2.5707 (12) Å (Sn1—Br3). These values are significantly longer than those reported for a related SnBr<sub>4</sub>(dioxane) complex (Bauer, Groy & Kouvetakis, 2002), which are in the range 2.5005 (7)–2.5045 (6) Å. The angles within the SnBr<sub>4</sub> square plane are nearly 90° [90.82 (3)° for Br2—Sn1—Br3] and the angles between the plane and the axis of the HN(CH<sub>3</sub>)<sub>2</sub> ligands are 86.18 (10)° (N4—Sn1—Br2) and 85.46 (10)° (N4—Sn1—Br3).

All H-atom positions were calculated based on idealized geometry. The H atoms were then allowed to ride on their bonding partners during the final stages of refinement. There is an indication of intermolecular interaction between one amine H atom and the nearest neighbor Br atom, since the Br2···H4A distance is 2.63 Å and the N4—H4A···Br2 angle is 150°.

## Experimental

SnBr<sub>4</sub>[HN(CH<sub>3</sub>)<sub>2</sub>]<sub>2</sub> is readily synthesized in toluene by direct combination of SnBr<sub>4</sub> with purified HN(CH<sub>3</sub>)<sub>2</sub>. This compound has been characterized by spectroscopic methods and combustion analysis. Single crystals have been grown by slowly cooling concentrated toluene solutions of the compound.

## Crystal data

[SnBr<sub>4</sub>(C<sub>2</sub>H<sub>7</sub>N)<sub>2</sub>]  
M<sub>r</sub> = 528.50  
Monoclinic, *P*2<sub>1</sub>/*c*  
*a* = 6.592 (4) Å  
*b* = 12.029 (7) Å  
*c* = 8.326 (5) Å  
 $\beta$  = 96.114 (11)°  
*V* = 656.5 (7) Å<sup>3</sup>  
*Z* = 2

*D<sub>x</sub>* = 2.674 Mg m<sup>-3</sup>  
Mo *K*α radiation  
Cell parameters from 3041 reflections  
 $\theta$  = 3.0–25.1°  
 $\mu$  = 14.08 mm<sup>-1</sup>  
*T* = 298 (2) K  
Block, colorless  
0.28 × 0.21 × 0.14 mm

## Data collection

Bruker SMART APEX diffractometer  
 $\omega$  scans  
Absorption correction: multi-scan (SADABS; Bruker, 2001)  
*T*<sub>min</sub> = 0.034, *T*<sub>max</sub> = 0.135  
5130 measured reflections

1161 independent reflections  
1028 reflections with *I* > 2σ(*I*)  
*R*<sub>int</sub> = 0.042  
 $\theta$ <sub>max</sub> = 25.1°  
*h* = -7 → 7  
*k* = -14 → 14  
*l* = -9 → 9

## Refinement

Refinement on *F*<sup>2</sup>  
*R* [*F*<sup>2</sup> > 2σ(*F*<sup>2</sup>)] = 0.026  
*wR* (*F*<sup>2</sup>) = 0.065  
*S* = 1.05  
1161 reflections  
53 parameters  
H-atom parameters constrained

$w = 1/[\sigma^2(F_o^2) + (0.0306P)^2 + 0.2351P]$   
where  $P = (F_o^2 + 2F_c^2)/3$   
( $\Delta/\sigma$ )<sub>max</sub> < 0.001  
 $\Delta\rho_{max} = 0.71 \text{ e } \text{Å}^{-3}$   
 $\Delta\rho_{min} = -0.73 \text{ e } \text{Å}^{-3}$   
Extinction correction: *SHELXTL*  
Extinction coefficient: 0.0021 (5)

Data collection: *SMART* (Bruker, 2002); cell refinement: *SAINT* (Bruker, 2002); data reduction: *SAINT*; program(s) used to solve structure: *SHELXTL* (Bruker, 1997); program(s) used to refine structure: *SHELXTL*; molecular graphics: *SHELXTL*; software used to prepare material for publication: *SHELXTL*.

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